
26. (amended) The capacitor of claim 23, wherein said annealed top conducting layer is a plasma enhanced annealed top conducting layer.

C²

27. (amended) The capacitor of claim 23, wherein said annealed top conducting layer is a remote plasma enhanced annealed top conducting layer.

28. (amended) The capacitor of claim 23, wherein said annealed top conducting layer is an ultraviolet light enhanced annealed top conducting layer.

98. (twice amended) A capacitor for a semiconductor device, said capacitor comprising:

C³

a bottom conducting layer;

an annealed dielectric layer formed over said bottom conducting layer; and

an annealed top conducting layer formed over said annealed dielectric layer, said top conducting layer comprising a metal oxide permeable to oxygen, wherein each of said bottom and annealed top conducting layers is formed of a material selected from the group consisting of platinum, platinum rhodium, platinum iridium, and tungsten nitride.
